






GERMANIUM POWER TRANSISTOR SELECTOR GUIDE (continued)


10 - AMP P ₀ = 85 W f _r = 0.7 MHz *P ₀ = 56 W *f _r = 1.0 MHz	HIGH-VOLTAGE LOW-SATURATION SWITCH 	h_{FE} $I_C = 3 A,$ $V_{CE} = 2 V$	V_{CEO} V_{CE}	80 V	120 V	160 V	V_{CES}	
				80 V	120 V	160 V	200 V	320 V
		20-50 20 min *		2N2526	2N2527	2N2528	MP3730*	MP3731*


15 - AMP P ₀ = 170 W f _r = 0.3 MHz	GENERAL PURPOSE SWITCH AND AMPLIFIER 	h_{FE} $I_C = 5 A,$ $V_{CE} = 2 V$	V_{CES} V_{CE}	40 V	50 V	70 V	80 V	
				40 V	50 V	70 V	80 V	
		20-40		2N2078	2N2077	2N2076	2N2075	
35-70		2N2082	2N2081	2N2080	2N2079			

15 - AMP P ₀ = 150 W f _r = 0.3 MHz	GENERAL PURPOSE SWITCH AND AMPLIFIER 	h_{FE} $I_C = 5 A,$ $V_{CE} = 2 V$	V_{CES} V_{CE}	40 V	45 V	50 V	70 V	80 V
				40 V	50 V	60 V	80 V	100 V
		20-40		2N441	2N442	2N443		
25-50					2N174	2N1100		
35-70		2N277	2N278	2N173	2N1099			

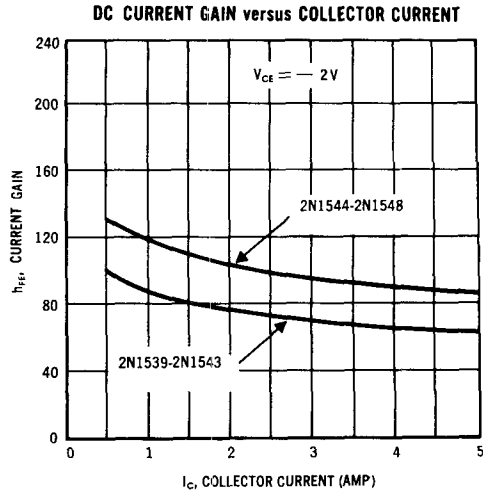
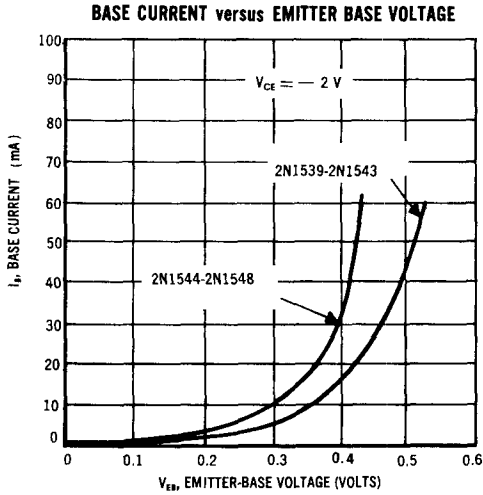
15 - AMP P ₀ = 106 W	HIGH-FREQUENCY SWITCH AND AMPLIFIER 	h_{FE} $I_C = 10 A,$ $V_{CE} = 2 V$	V_{CES} V_{CE}	30 V	45 V	60 V	75 V	
				40 V	60 V	80 V	100 V	
		10-30 f _r = 0.55 MHz		2N1549	2N1550	2N1551	2N1552	
30-60 f _r = 0.4 MHz		2N1553	2N1554	2N1555	2N1556			
50-100 f _r = 0.4 MHz		2N1557	2N1558	2N1559	2N1560			

20 - AMP P ₀ = 85 W f _r = 18 MHz	HIGH-SPEED SWITCH 	h_{FE} $I_C = 10 A,$ $V_{CE} = 2 V$	V_{CEO} V_{CE}	50 V		75 V		100 V
				80 V		120 V		140 V
		25-100		2N2832		2N2833		2N2834

25 - AMP P ₀ = 106 W f _r = 0.4 MHz	HIGH DC GAIN SWITCH 	h_{FE} $I_C = 25 A,$ $V_{CE} = 1 V$	V_{CES} V_{CE}	35 V		60 V		75 V
				50 V		80 V		100 V
		15-65		2N1162		2N1164		2N1166
		2N1163†		2N1165†		2N1167†		

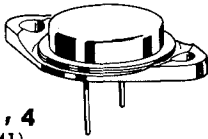
25 - AMP P ₀ = 75 W f _r = 10 MHz	HIGH DC GAIN LOW-SATURATION SWITCH 	h_{FE} $I_C = 5 A,$ $V_{CE} = 2 V$	$V_{CE(sat)}$ $I_C = 25 A,$ $I_E = 2.5 A$ V_{CE}	0.5 V				
				15 V				
		200-800				2N2912		

2N1539 thru 2N1548 (continued)



2N1549, A thru 2N1560, A (GERMANIUM)
2N1549A JAN thru 2N1556A JAN
2N1560A JAN AVAILABLE)

$V_{CB} = 40-100 \text{ V}$
 $I_C = 15 \text{ A}$
 $P_D = 106 \text{ W}$



CASE 3, 4
(TO-3, 41)

PNP germanium power transistors for switching and amplifier applications in high-reliability equipment.

For units with solder lugs attached, specify devices MP1549A etc. (TO-41 package)

MAXIMUM RATINGS

Apply to corresponding "Hi-Rel" Series Also

Rating	Symbol	2N1549 2N1553 2N1557	2N1550 2N1554 2N1558	2N1551 2N1555 2N1559	2N1552 2N1556 2N1560	Units
Collector-Emitter Voltage	V_{CEX}	40	60	80	100	Vdc
Collector-Emitter Voltage	V_{CES}^*	30	45	60	75	Vdc
Collector-Emitter Voltage	V_{CEO}^*	20	30	40	50	Vdc
Collector-Base Voltage	V_{CB}	40	60	80	100	Vdc
Emitter-Base Voltage	V_{EB}	20	30	40	50	Vdc
Collector Current (Continuous)	I_C	15	15	15	15	Amp
Collector Current (Peak)	I_C	20	20	20	20	Amp
Collector Junction Temperature	T_J	-65 to +110				$^{\circ}\text{C}$
Collector Dissipation (25 C Case Temp.)	P_D	106	106	106	106	Watts
Thermal Resistance	θ_{JC}	0.8				$^{\circ}\text{C}/\text{W}$

*To avoid excessive heating of collector junction, perform this test with a sweep method.

2N1549 thru 2N1560 (continued)

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Collector-Base Cutoff Current ($V_{CB} = 25\text{ V}$) 2N1549, 2N1553, 2N1557	I_{CBO1}	-	3.0	mA
($V_{CB} = 40\text{ V}$) 2N1550, 2N1554, 2N1558		-	3.0	
($V_{CB} = 55\text{ V}$) 2N1551, 2N1555, 2N1559		-	3.0	
($V_{CB} = 65\text{ V}$) 2N1552, 2N1556, 2N1560		-	3.0	
Collector-Base Cutoff Current ($V_{CB} = 2\text{ V}$) ($V_{CB} = 1/2 BV_{CES}$ rating; $T_C = +90^\circ\text{C}$)	I_{CBO}	-	0.2	mA
		-	20	
Emitter-Base Cutoff Current ($V_{EB} = 12\text{ V}$)	I_{EBO}	-	0.5	mA
Collector-Emitter Breakdown Voltage ($I_C = 300\text{ mA}$) 2N1549, 2N1553, 2N1557 2N1550, 2N1554, 2N1558 2N1551, 2N1555, 2N1559 2N1552, 2N1556, 2N1560	BV_{CES}	30	-	volts
		45	-	
		60	-	
		75	-	
Collector-Emitter Leakage Current ($V_{BE} = 1.0\text{ V}$, V_{CE} @ rated BV_{CBO})	I_{CEX}	-	20	mA
Collector-Emitter Breakdown Voltage* ($I_C = 300\text{ mA}$, $I_B = 0$) 2N1549, 2N1553, 2N1557 2N1550, 2N1554, 2N1558 2N1551, 2N1555, 2N1559 2N1552, 2N1556, 2N1560	BV_{CEO}^*	20	-	volts
		30	-	
		40	-	
		50	-	
Collector-Base Breakdown Voltage ($I_C = 20\text{ mA}$) 2N1549, 2N1553, 2N1557 2N1550, 2N1554, 2N1558 2N1551, 2N1555, 2N1559 2N1552, 2N1556, 2N1560	BV_{CBO}	40	-	volts
		60	-	
		80	-	
		100	-	
Current Gain ($V_{CE} = 2.0\text{ V}$, $I_C = 10\text{ A}$) 2N1549 - 2N1552 2N1553 - 2N1556 2N1557 - 2N1560	h_{FE1}	10	30	-
		30	60	
		50	100	
Base-Emitter Drive Voltage ($I_C = 10\text{ A}$, $I_B = 1.0\text{ A}$) 2N1549 - 2N1552 2N1553 - 2N1556 2N1557 - 2N1560	V_{BE}	-	1.3	volts
		-	1.0	
		-	0.7	
Collector Saturation Voltage ($I_C = 10\text{ A}$, $I_B = 1.0\text{ A}$) 2N1549 - 2N1552 2N1553 - 2N1556 2N1557 - 2N1560	$V_{CE(sat)}$	-	1.0	volts
		-	0.7	
		-	0.5	

Characteristics apply to corresponding A type numbers also.

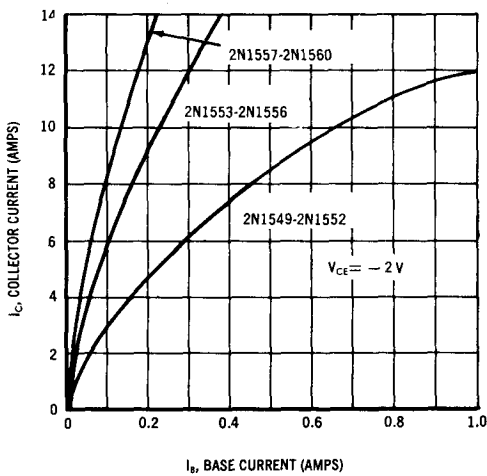
*To avoid excessive heating of collector junction, perform this test with a sweep method.

2N1549 thru 2N1560 (continued)

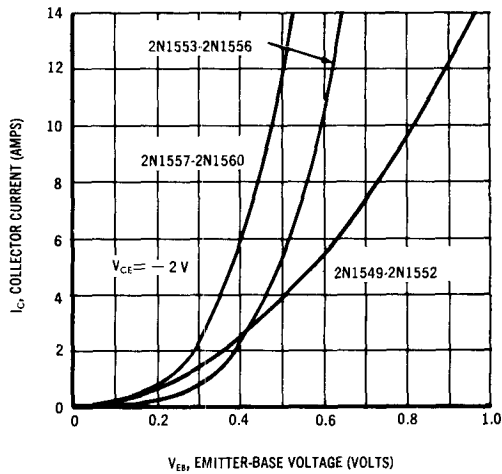
ELECTRICAL CHARACTERISTICS (continued)

Characteristic	Symbol	Min	Max	Unit	
Transconductance ($V_{CE} = 2.0 \text{ V}$, $I_C = 10 \text{ A}$)	g_{FE}			mhos	
		2N1549 - 2N1552	6		18
		2N1553 - 2N1556	8		30
		2N1557 - 2N1560	12		40
Frequency Cutoff	f_{ae}		Typ	kHz	
		2N1549 - 2N1552	10		
		2N1553 - 2N1556	6		
		2N1557 - 2N1560	5		

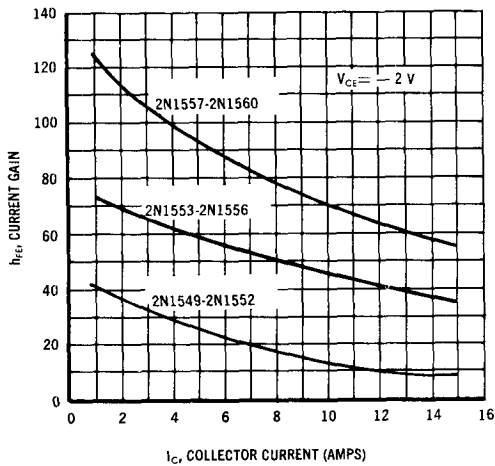
COLLECTOR CURRENT versus BASE CURRENT



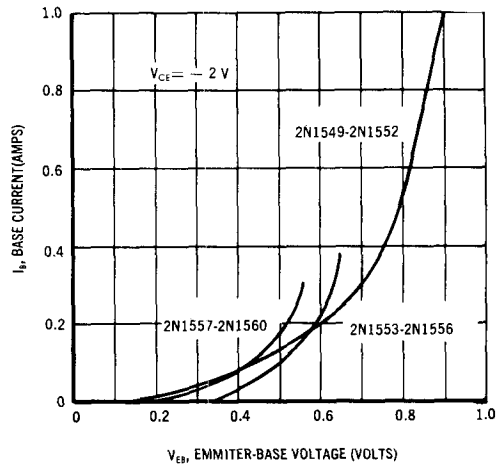
COLLECTOR CURRENT versus EMITTER-BASE VOLTAGE



CURRENT GAIN versus COLLECTOR CURRENT



BASE CURRENT versus EMITTER-BASE VOLTAGE

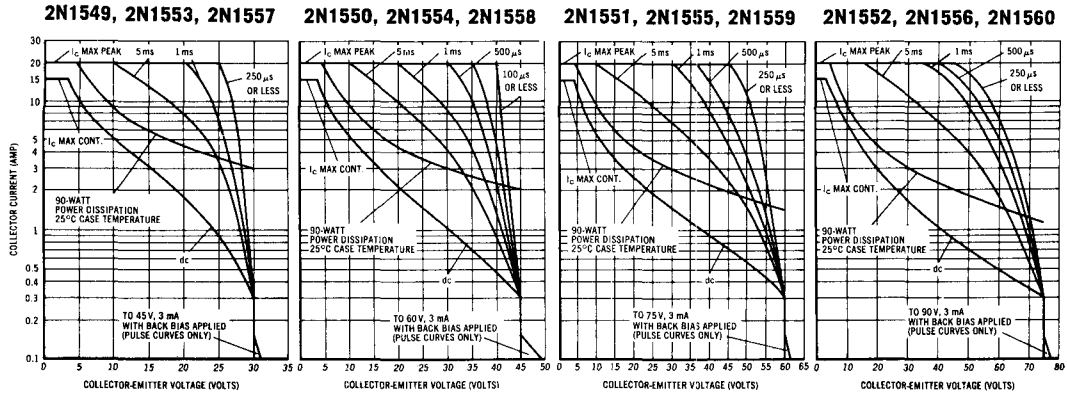


2N1549 thru 2N1560 (continued)

SAFE OPERATING AREAS

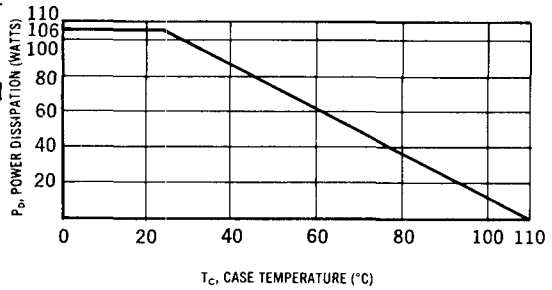
The Safe Operating Area Curves indicate I_C — V_{CE} limits below which the device will not go into secondary breakdown. Collector load lines for specific circuits must fall within the applicable Safe Area to avoid causing a collector-emitter short.

(Duty cycle of the excursions make no significant change in these safe areas.) To insure operation below the maximum T_J , the power-temperature derating curve must be observed for both steady state and pulse power conditions.

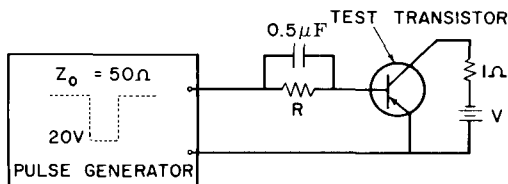


POWER-TEMPERATURE DERATING CURVE

The maximum continuous power is related to maximum junction temperature, by the thermal resistance factor. For dc or frequencies below 25 Hz the transistor must be operated within the constant $P_D = V_c \times I_c$ hyperbolic curve. This curve has a value of 106 watts at case temperatures of 25°C and is 0 watts at 110°C with a linear relation between the two temperatures such that P_D allowable = $\frac{110 - T_c}{0.8}$



SWITCHING TIME MEASURING UNIT



Devices	Conditions*			Typical Switching Times		
	I_C (Amp)	V (Volts)	R (ohms)	$t_d + t_r$ (μs)	t_f (μs)	t_r (μs)
2N1549 -52	10	10	10	5	2	10
2N1553 -56	10	10	30	10	5	25
2N1557 -60	10	10	50	10	5	25

* Input Pulse Repetition Rate = 2 kHz,
Pulse Width = 50 μs